

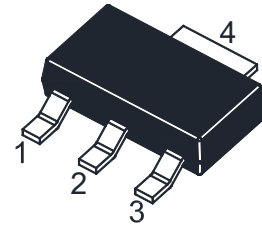
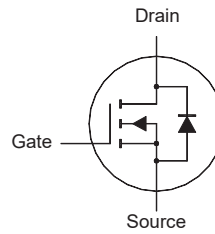
## N-Channel Enhancement Mode MOSFET

### Features

- AEC-Q101 Qualified
- Surface-mounted package
- Halogen and Antimony Free(HAF), RoHS compliant

### Applications

- BLDC Motor drive applications
- Battery powered circuits
- Synchronous rectifier applications
- Resonant mode power supplies



1.Gate 2.Drain 3.Source 4.Dr  
SOT-223 Plastic Package

### Key Parameters

Parameter	Value	Unit
$BV_{DSS}$	100	V
$R_{DS(ON)}$ Max	115 @ $V_{GS} = 10$ V	m $\Omega$
	125 @ $V_{GS} = 4.5$ V	
$V_{GS(th)}$ typ	1.6	V
$Q_g$ typ	20 @ $V_{GS} = 10$ V	nC

### Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_c = 25^\circ\text{C}$	5
		$T_c = 100^\circ\text{C}$	3.5
Peak Drain Current, Pulsed <sup>1)</sup>	$I_{DM}$	20	A
Single-Pulse Avalanche Current	$I_{AS}$	5	A
Single-Pulse Avalanche Energy <sup>2)</sup>	$E_{AS}$	3.7	mJ
Total Power Dissipation	$P_{tot}$	10	W
Operating Junction and Storage Temperature Range	$T_j, T_{stg}$	- 55 to + 175	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	15	$^\circ\text{C/W}$
Thermal Resistance - Junction to Ambient <sup>3)</sup>	$R_{\theta JA}$	45	$^\circ\text{C/W}$
Thermal Resistance - Junction to Ambient <sup>4)</sup> Steady State	$R_{\theta JA}$	100	$^\circ\text{C/W}$

<sup>1)</sup> Pulse Test: Pulse Width  $\leq 100$   $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ , Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)} = 175^\circ\text{C}$ .

<sup>2)</sup> Limited by  $T_{J(MAX)}$ , starting  $T_j = 25^\circ\text{C}$ ,  $L = 0.3$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 5$  A,  $V_{GS} = 10$  V.

<sup>3)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate,  $t < 10$  s.

<sup>4)</sup> Device mounted on FR-4 substrate PC board, minimum recommended footprint.

Characteristics at  $T_a = 25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>					
Drain-Source Breakdown Voltage at $I_D = 250\ \mu\text{A}$	$BV_{DSS}$	100	-	-	V
Drain-Source Leakage Current at $V_{DS} = 80\ \text{V}$	$I_{DSS}$	-	-	1	$\mu\text{A}$
Gate Leakage Current at $V_{GS} = \pm 20\ \text{V}$	$I_{GSS}$	-	-	$\pm 100$	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at $V_{GS} = 10\ \text{V}$ , $I_D = 4\ \text{A}$ at $V_{GS} = 4.5\ \text{V}$ , $I_D = 3\ \text{A}$	$R_{DS(on)}$	- -	106 -	115 125	m $\Omega$
<b>DYNAMIC PARAMETERS</b>					
Forward Transconductance at $V_{DS} = 5\ \text{V}$ , $I_D = 4\ \text{A}$	$g_{fs}$	-	8	-	S
Gate Resistance at $V_{DS} = 0\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$	$R_g$	-	1.1	-	$\Omega$
Input Capacitance at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$	$C_{iss}$	-	1155	-	pF
Output Capacitance at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$	$C_{oss}$	-	28	-	pF
Reverse Transfer Capacitance at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$	$C_{rss}$	-	25	-	pF
Gate Charge Total at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 10\ \text{V}$ , $I_D = 4\ \text{A}$ at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 4.5\ \text{V}$ , $I_D = 4\ \text{A}$	$Q_g$	- -	20 9	- -	nC
Gate to Source Charge at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 10\ \text{V}$ , $I_D = 4\ \text{A}$	$Q_{gs}$	-	4	-	nC
Gate to Drain Charge at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 10\ \text{V}$ , $I_D = 4\ \text{A}$	$Q_{gd}$	-	2	-	nC
Turn-On Delay Time at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 10\ \text{V}$ , $I_D = 4\ \text{A}$ , $R_g = 3.3\ \Omega$	$t_{d(on)}$	-	14	-	ns
Turn-On Rise Time at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 10\ \text{V}$ , $I_D = 4\ \text{A}$ , $R_g = 3.3\ \Omega$	$t_r$	-	4	-	ns
Turn-Off Delay Time at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 10\ \text{V}$ , $I_D = 4\ \text{A}$ , $R_g = 3.3\ \Omega$	$t_{d(off)}$	-	13	-	ns
Turn-Off Fall Time at $V_{DS} = 50\ \text{V}$ , $V_{GS} = 10\ \text{V}$ , $I_D = 4\ \text{A}$ , $R_g = 3.3\ \Omega$	$t_f$	-	2	-	ns
<b>Body-Diode PARAMETERS</b>					
Drain-Source Diode Forward Voltage at $I_S = 1\ \text{A}$ , $V_{GS} = 0\ \text{V}$	$V_{SD}$	-	-	1.2	V
Body-Diode Continuous Current	$I_S$	-	-	5	A
Body-Diode Continuous Current, Pulsed	$I_{SM}$	-	-	20	A
Body Diode Reverse Recovery Time at $I_S = 4\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$	$t_{rr}$	-	21	-	ns
Body Diode Reverse Recovery Charge at $I_S = 4\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$	$Q_{rr}$	-	22	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

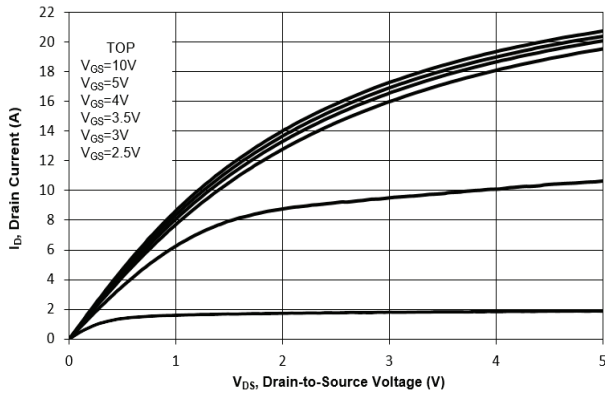


Fig. 2 Typical Transfer Characteristics

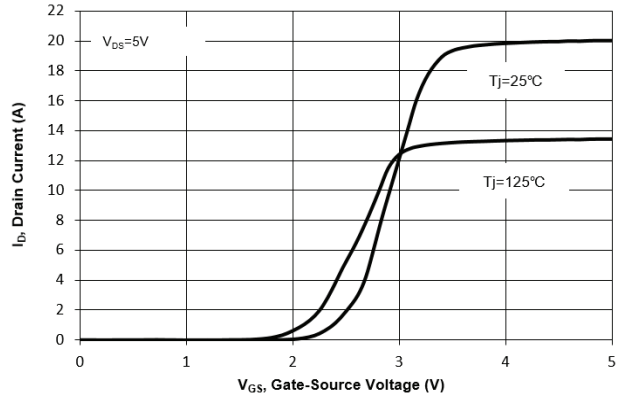


Fig. 3 on-Resistance vs Drain Current

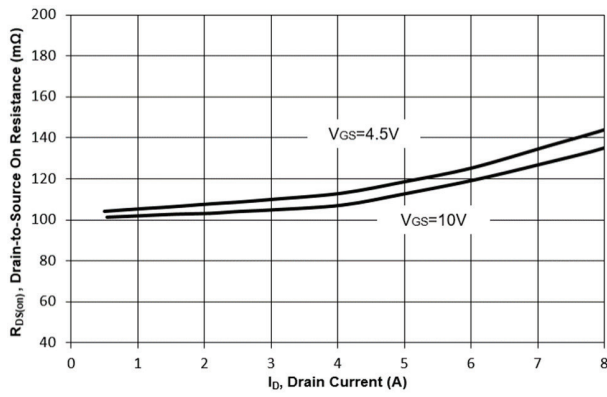


Fig. 4 on-Resistance vs. Gate to Source Voltage

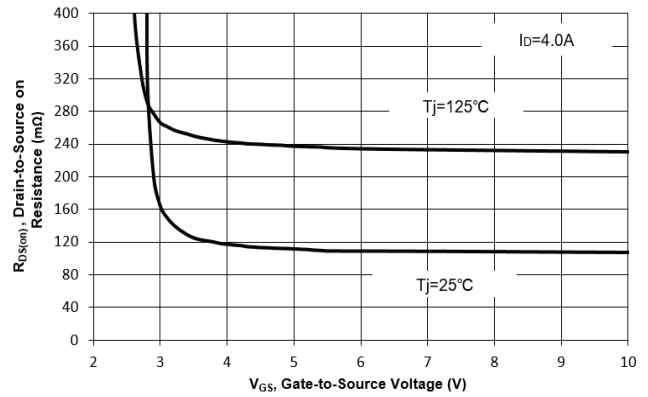


Fig. 5 on-Resistance vs. TJ

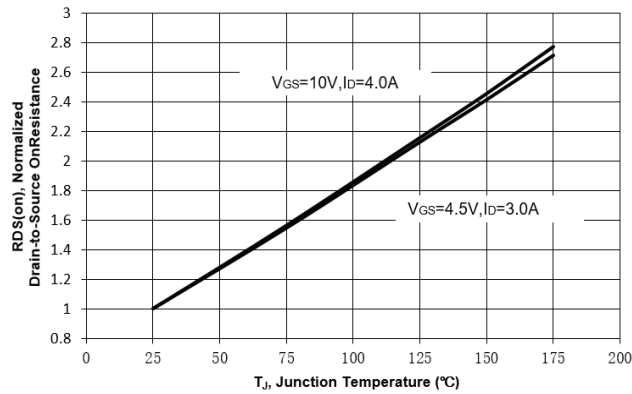
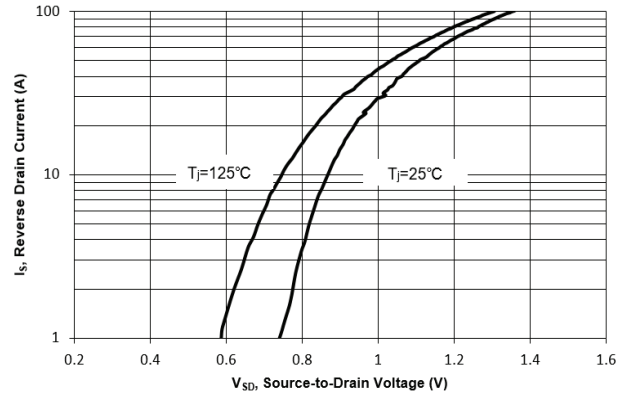


Fig. 6 Typical Body Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

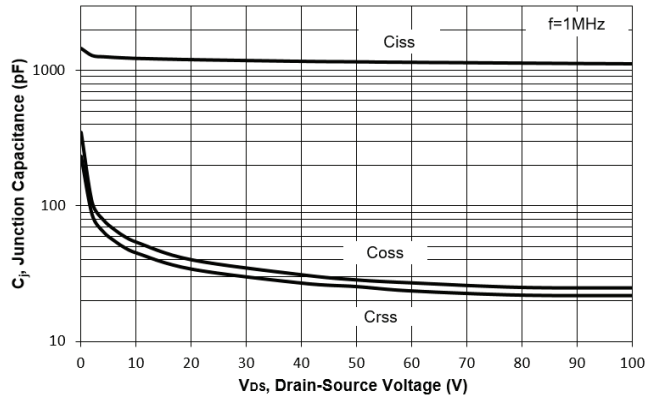


Fig. 8 Drain-Source Leakage Current vs. Tj

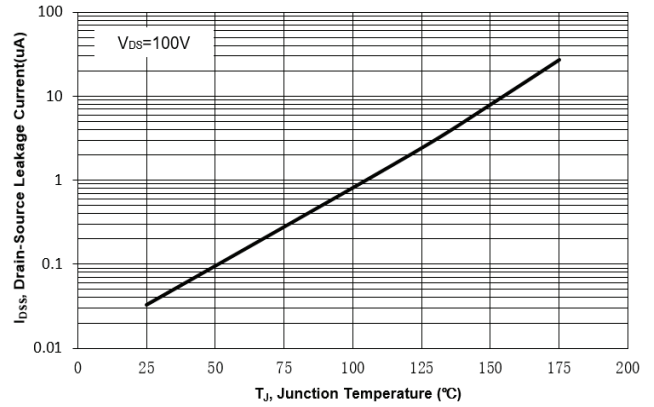


Fig. 9 V(BR)DSS vs. Junction Temperature

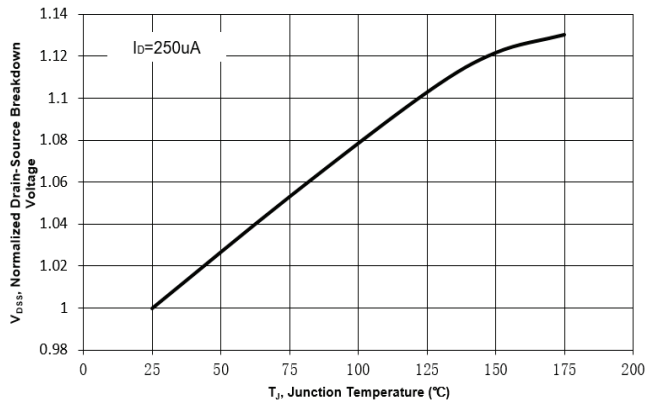


Fig. 10 Gate Threshold Variation vs. Tj

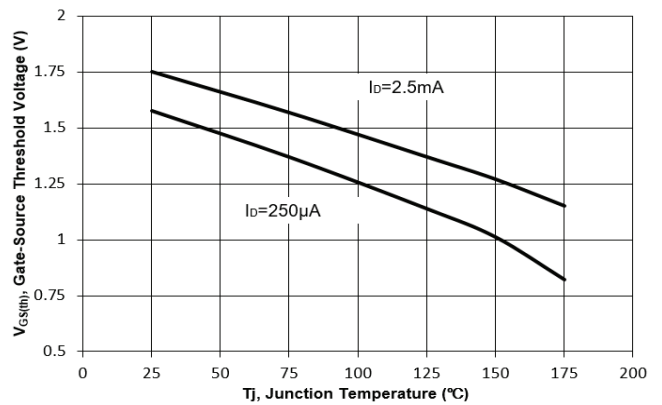


Fig. 11 Gate Charge

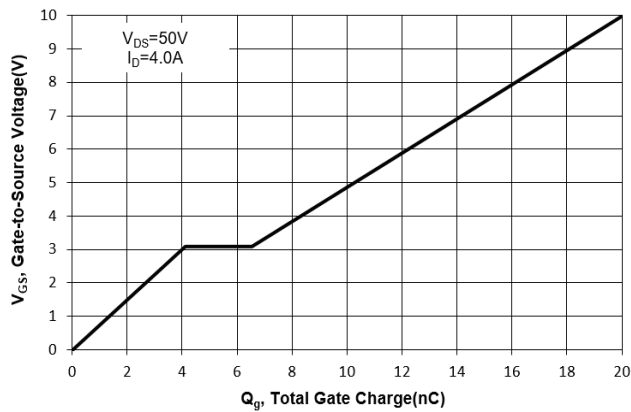
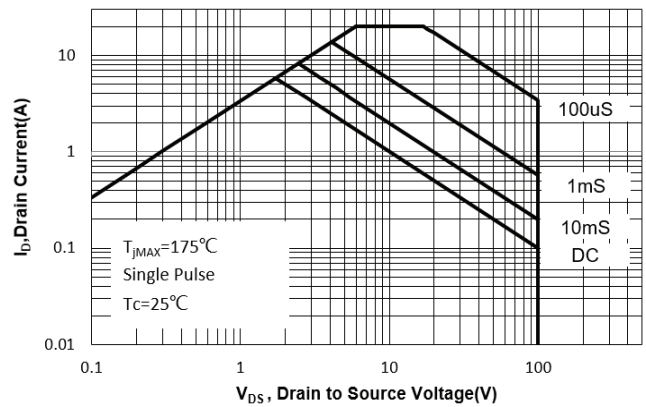


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance( $Z_{\theta JC}$ )

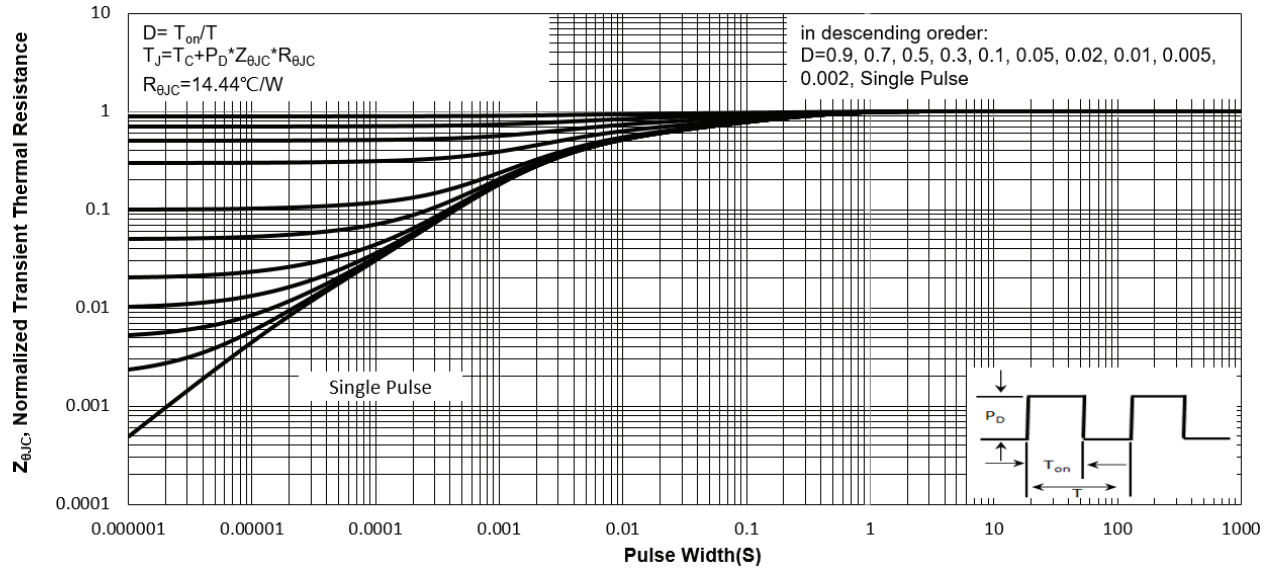
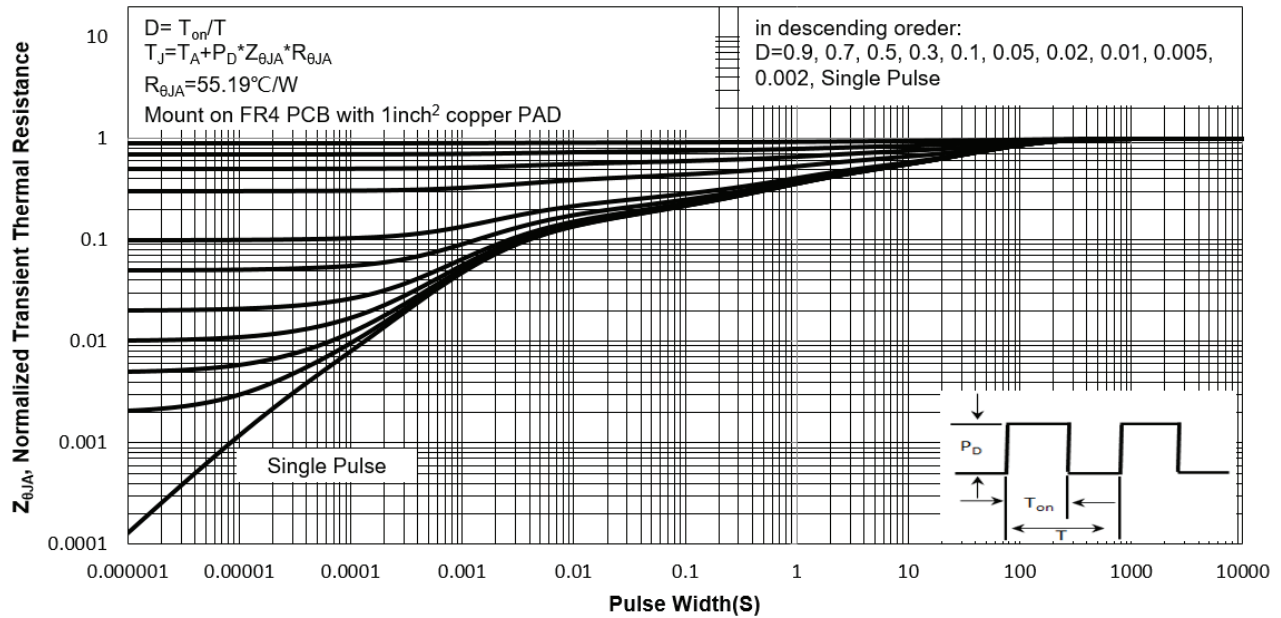


Fig. 14 Normalized Maximum Transient Thermal Impedance( $Z_{\theta JA}$ )



Test Circuits

Fig.1-1 Switching times test circuit

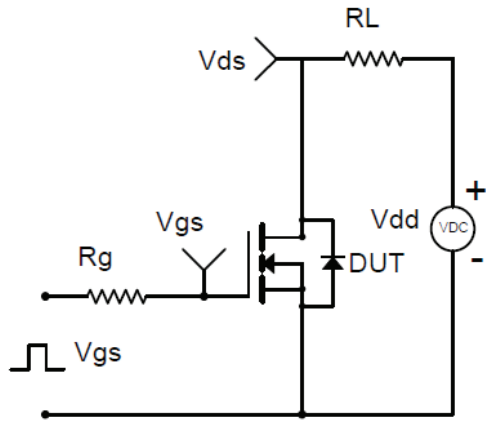


Fig.1-2 Switching Waveform

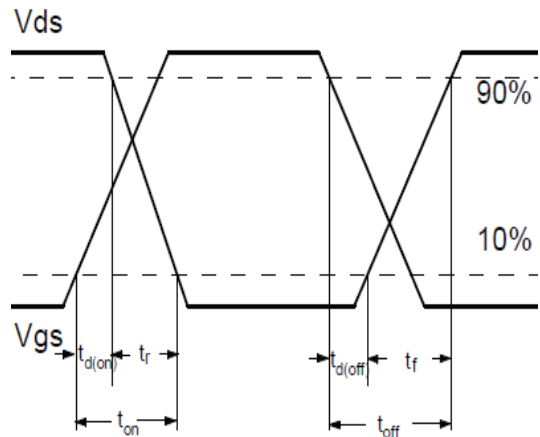


Fig.2-1 Gate charge test circuit

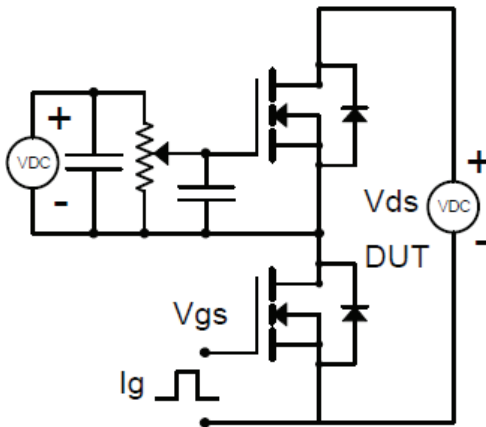


Fig.2-2 Gate charge waveform

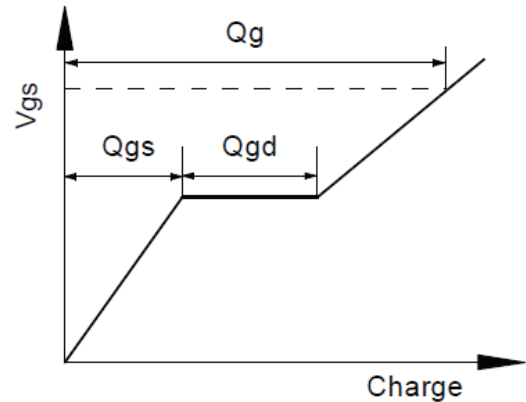


Fig.3-1 Avalanche test circuit

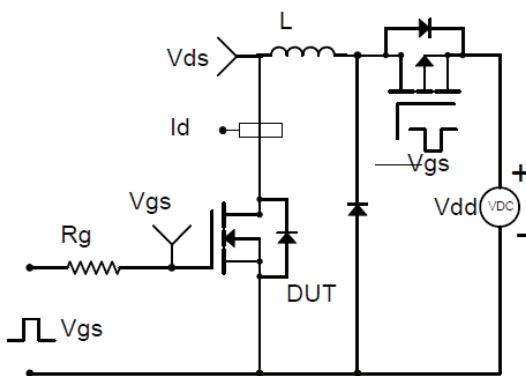
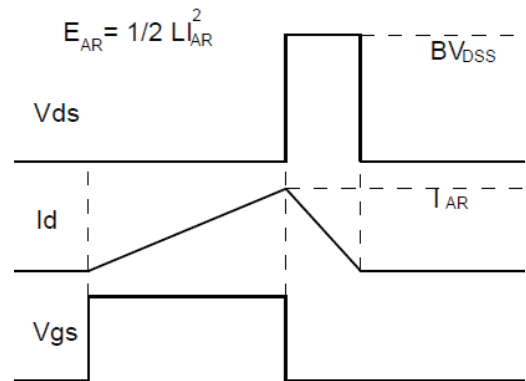
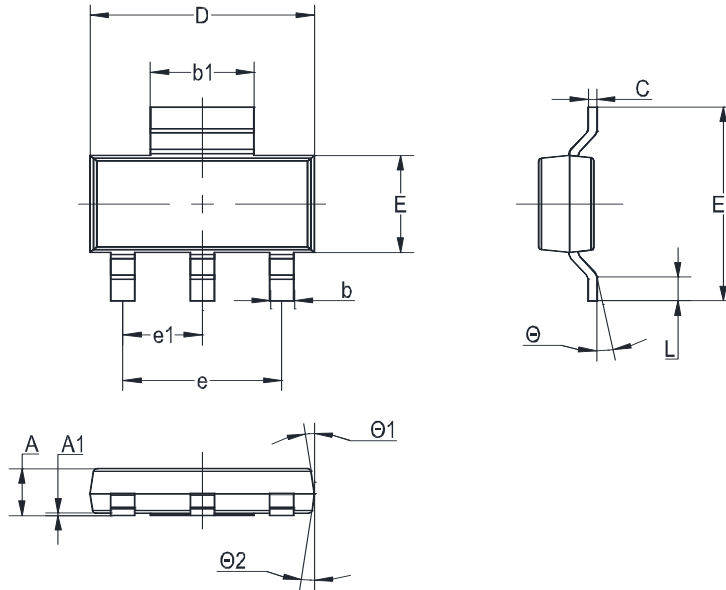


Fig.3-2 Avalanche waveform



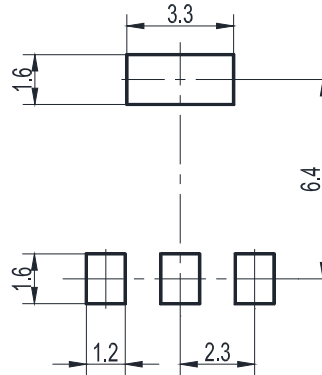
Package Outline (Dimensions in mm)

SOT-223



Unit	A	A1	b	b1	C	D	E	E1	e	e1	L	Θ	Θ1	Θ2
mm	1.8	0.1	0.8	3.1	0.32	6.7	3.7	7.3	4.6	2.3	1.1	10°	7°	7°
	1.5	MAX	0.6	2.9	0.22	6.3	3.3	6.7	TYP	TYP	0.7	0°	0°	0°

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Marking information

" TQ10N1K1LS " = Part No.

" \*\*\*\*\* " = Date Code Marking

Font type: Arial



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